

**BYV80MW-650PT2** 

Ultrafast power diode Rev.02 - 25 January 2024

**Product data sheet** 

## **1. General description**

Ultrafast power diode in a TO247-2L plastic package.



## 2. Features and benefits

- 650V FRD
- Low thermal resistance
- Low forward voltage drop
- · Low leakage current & reverse recovery current
- Enhanced Eas capability suitable for industrical application
- Reduces switching losses in associated MOSFET or IGBT
- Package meets UL94 V-0 which guaranteed by Epoxy Mold Compound

## 3. Applications

- NPC-I in UPS
  - LLC in EV charger
  - PFC in air conditioner or welding machine
  - Power Factor Correction (PFC)
- 2<sup>nd</sup> rectification in HB/FB SMPS

## 4. Quick reference data

Table 4. Outals as forman a state

	uick reference data						
Symbol	Parameter	Conditions	Values				Unit
Absolute	maximum rating						
$V_{\text{RRM}}$	repetitive peak reverse voltage			6	50		V
$I_{F(AV)}$	average forward current	δ = 0.5; T <sub>mb</sub> ≤ 114 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3		80			A
I <sub>FRM</sub>	repetitive peak forward current	δ = 0.5; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 114 °C; square-wave pulse	160			A	
I <sub>FSM</sub>	non-repetitive peak forward current	$t_{\rm p}$ = 10 ms; $T_{\rm j(init)}$ = 25 °C; sine-wave pulse; Fig. 4				A	
		$t_{\rm p}$ = 8.3 ms; $T_{\rm j(init)}$ = 25 °C; sine-wave pulse			А		
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics		-				
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 80 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	1.40	1.70	V
		I <sub>F</sub> = 80 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	1.20	1.40	V
Dynamic	characteristics				,		
t <sub>rr</sub>	reverse recovery time	I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 100 A/μs; T <sub>i</sub> = 25 °C; <u>Fig. 7</u>		-	46	-	ns

# 5. Pinning information

Table 2. F	inning infor	mation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode		К — Ң — А
2	А	anode		001aaa020
mb	mb	mounting base; connected to cathode	К ТО247-2L	

# 6. Ordering information

Table 3. Ordering information							
Type number	Package	Orderable part number	Packing	Small packing	Package	Package	
	name		method	quantity	version	issue date	
BYV80MW-650PT2	TO247-2L	BYV80MW-650PT2Q	Tube	30	TO247L-2L (L)	10-Nov-2020	
					TO247P-2L (P)	31-Mar-2023	

# 7. Marking

Table 4	Marking	codes
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Type number	Marking codes		
	Assembly factory: L	Assembly factory: P	
BYV80MW-650PT2	BYV80MW 650PT2 PJLxxxx xx	BYV80MW 650PT2 PJPxxxx xx	

## 8. Limiting values

## Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{\text{RRM}}$	repetitive peak reverse voltage		650	V
$V_{\text{RWM}}$	crest working reverse voltage		650	V
V <sub>R</sub>	reverse voltage	DC	650	V
$I_{F(AV)}$	average forward current	δ = 0.5; T <sub>mb</sub> ≤ 114 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	80	A
I <sub>FRM</sub>	repetitive peak forward current	δ = 0.5; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 114 °C; square-wave pulse	160	A
I <sub>FSM</sub>	non-repetitive peak forward current	t <sub>p</sub> = 10 ms; T <sub>j(init)</sub> = 25 °C; sine-wave pulse; Fig. 4	730	A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	800	A
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; sine-wave pulse	2665	A <sup>2</sup> s
T <sub>stg</sub>	storage temperature		-65 to 175	°C
T <sub>j</sub>	junction temperature		-65 to 175	°C

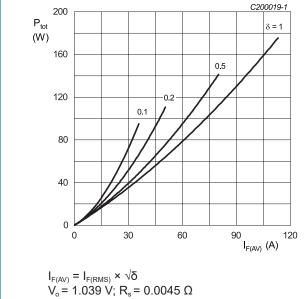
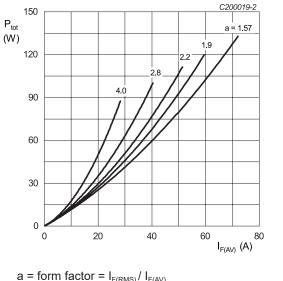
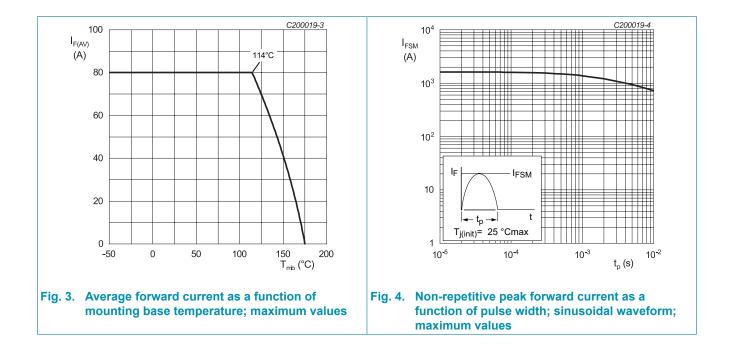


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



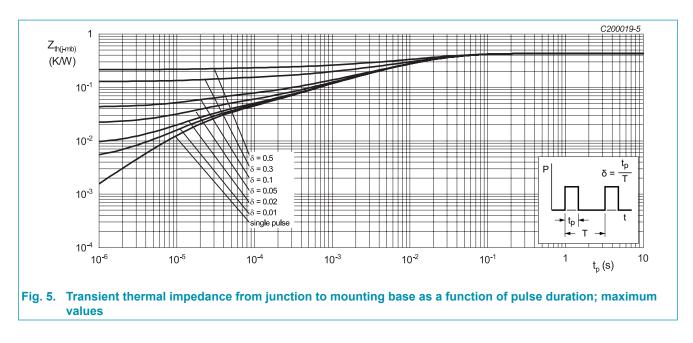
 $\begin{array}{l} \textbf{a} = form \ factor = I_{F(RMS)} / \ I_{F(AV)} \\ V_o = 1.039 \ V; \ R_s = 0.0045 \ \Omega \\ \hline \textbf{Fig. 2. Forward power dissipation as a function of} \\ \textbf{average forward current; sinusoidal waveform;} \\ \textbf{maximum values} \end{array}$ 

**BYV80MW-650PT2 Ultrafast power diode** 



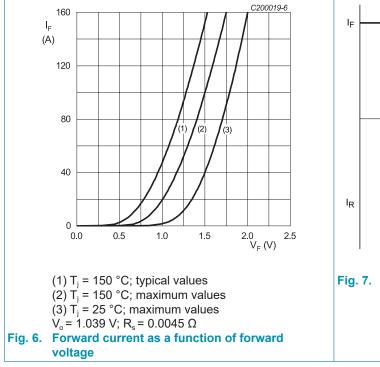
## 9. Thermal characteristics

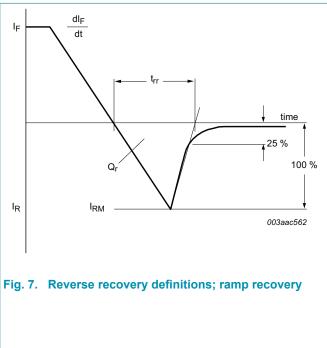
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	0.43	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	40	-	K/W



# **10. Characteristics**

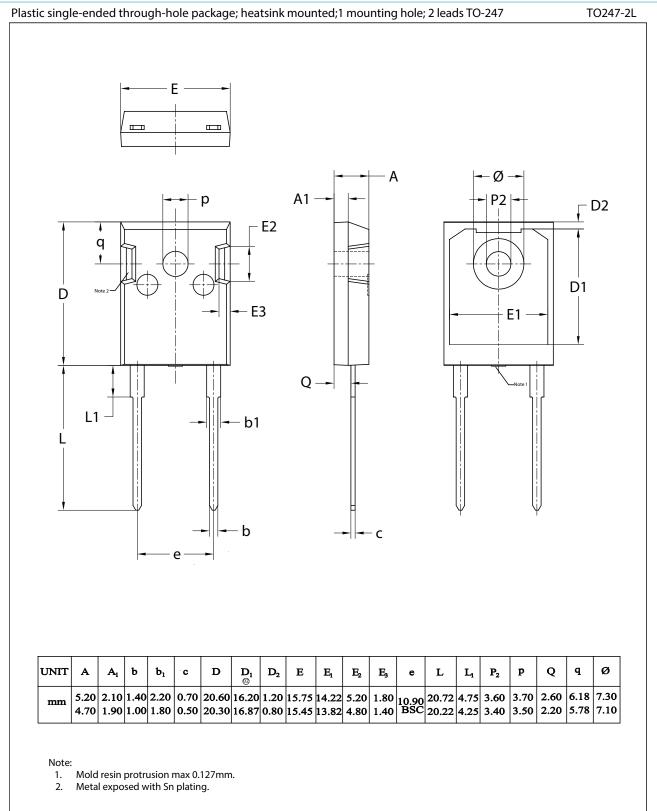
Table 7. Cl	naracteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 80 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	1.40	1.70	V
		I <sub>F</sub> = 80 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	1.20	1.40	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 650 V; T <sub>j</sub> = 25 °C	-	0.5	30	μA
		V <sub>R</sub> = 650 V; T <sub>j</sub> = 150 °C	-	-	5	mA
Dynamic	characteristics	·				
t <sub>rr</sub>	reverse recovery time	$I_F = 0.5 \text{ A}; I_R = 1 \text{ A}; I_r = 0.25 \text{ A};$ $T_j = 25 \text{ °C}$	-	90	-	ns
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	46	-	ns
		$I_F = 50 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	85	-	ns
		$I_{F} = 50 \text{ A};  V_{R} = 400 \text{ V};  dI_{F}/dt = 500  A/\mu\text{s}; \\ T_{j} = 125 ^{\circ}\text{C};  \underline{Fig. 7}$	-	150	-	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 50 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	16.5	-	A
		$I_F = 50 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	30.5	-	A
Qr	recovered charge	$I_F = 50 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$	-	700	-	nC
		$I_F = 50 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	2250	-	nC
Eas	non-repetitive analanche energy	T <sub>j</sub> = 25 °C	68	-	-	mJ



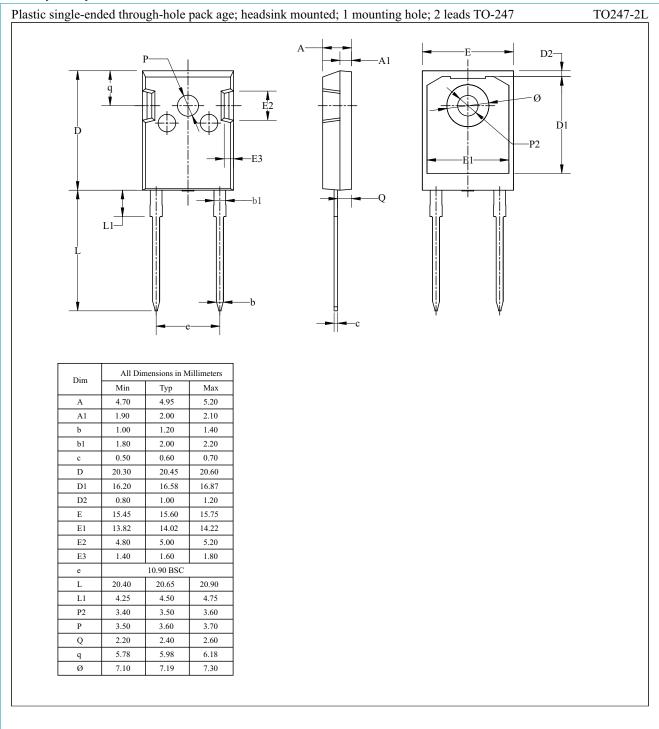


## **11. Package outline**

## Assembly factory: L



## Assembly factory: P



# BYV80MW-650PT2

### Ultrafast power diode

## 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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- [2] The term 'short data sheet' is explained in section "Definitions".
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